Jen-Inn Chyi

List of Publications by Year
in descending order

336 papers	6,247 citations	71102 41 h-index	102487 66 g-index
336 all docs	336 docs citations	336 times ranked	4999 citing authors

#	Article	IF	Citations
1	Resonant cavity-enhanced (RCE) photodetectors. IEEE Journal of Quantum Electronics, 1991, 27, 2025-2034.	1.9	308
2	Efficient Single-Photon Sources Based on Low-Density Quantum Dots in Photonic-Crystal Nanocavities. Physical Review Letters, 2006, 96, 117401.	7.8	244
3	Dependence of composition fluctuation on indium content in InGaN/GaN multiple quantum wells. Applied Physics Letters, 2000, 77, 2988-2990.	3.3	223
4	Beyond the Debye length in high ionic strength solution: direct protein detection with field-effect transistors (FETs) in human serum. Scientific Reports, 2017, 7, 5256.	3.3	173
5	In0.6Ga0.4As/GaAs quantum-dot infrared photodetector with operating temperature up to 260 K. Applied Physics Letters, 2003, 82, 1986-1988.	3.3	130
6	High sensitivity cardiac troponin I detection in physiological environment using AlGaN/GaN High Electron Mobility Transistor (HEMT) Biosensors. Biosensors and Bioelectronics, 2018, 100, 282-289.	10.1	128
7	AlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2002, 81, 1729-1731.	3.3	120
8	Growth of InSb and InAs1â˜'xSbxon GaAs by molecular beam epitaxy. Applied Physics Letters, 1988, 53, 1092-1094.	3.3	110
9	MgO/p-GaN enhancement mode metal-oxide semiconductor field-effect transistors. Applied Physics Letters, 2004, 84, 2919-2921.	3.3	104
10	Impact of localized states on the recombination dynamics in InGaN/GaN quantum well structures. Journal of Applied Physics, 2002, 92, 4441-4448.	2.5	100
11	Gd2O3/GaN metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2000, 77, 3230-3232.	3.3	96
12	GaN electronics for high power, high temperature applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 227-231.	3.5	95
13	Breakdown voltage and reverse recovery characteristics of free-standing GaN Schottky rectifiers. IEEE Transactions on Electron Devices, 2002, 49, 32-36.	3.0	88
14	Photocurrent studies of the carrier escape process from InAs self-assembled quantum dots. Physical Review B, 2000, 62, 6959-6962.	3.2	81
15	Tuning the energy levels of self-assembled InAs quantum dots by rapid thermal annealing. Applied Physics Letters, 2000, 76, 691-693.	3.3	80
16	Spatial manipulation of nanoacoustic waves with nanoscale spot sizes. Nature Nanotechnology, 2007, 2, 704-708.	31.5	80
17	High voltage GaN Schottky rectifiers. IEEE Transactions on Electron Devices, 2000, 47, 692-696.	3.0	77
18	Resonant cavity enhanced AlGaAs/GaAs heterojunction phototransistors with an intermediate InGaAs layer in the collector. Applied Physics Letters, 1990, 57, 750-752.	3.3	76

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19	Interdiffusion of In and Ga in InGaN/GaN multiple quantum wells. Applied Physics Letters, 2001, 78, 314-316.	3.3	75
20	Carrier effects on the excitonic absorption in GaAs quantum-well structures: Phase-space filling. Physical Review B, 1990, 42, 5147-5153.	3.2	73
21	Matrix dependence of strain-induced wavelength shift in self-assembled InAs quantum-dot heterostructures. Applied Physics Letters, 2000, 76, 1567-1569.	3.3	73
22	Mechanism of luminescence in InGaN/GaN multiple quantum wells. Applied Physics Letters, 2000, 76, 3712-3714.	3.3	73
23	Comparison of GaN p-i-n and Schottky rectifier performance. IEEE Transactions on Electron Devices, 2001, 48, 407-411.	3.0	71
24	AlGaN/GaN HEMT based liquid sensors. Solid-State Electronics, 2004, 48, 351-353.	1.4	68
25	Extremely High Saturation Current-Bandwidth Product Performance of a Near-Ballistic Uni-Traveling-Carrier Photodiode With a Flip-Chip Bonding Structure. IEEE Journal of Quantum Electronics, 2010, 46, 80-86.	1.9	64
26	Vertical and lateral GaN rectifiers on free-standing GaN substrates. Applied Physics Letters, 2001, 79, 1555-1557.	3.3	63
27	Material properties of compositional graded InxGa1â^'xAs and InxAl1â^'xAs epilayers grown on GaAs substrates. Journal of Applied Physics, 1996, 79, 8367-8370.	2.5	62
28	Direct measurement of piezoelectric field in In[sub 0.23]Ga[sub 0.77]N/GaN multiple quantum wells by electrotransmission spectroscopy. Journal of Applied Physics, 2002, 91, 531.	2.5	59
29	Nanostructures and carrier localization behaviors of green-luminescence InGaN/GaN quantum-well structures of various silicon-doping conditions. Applied Physics Letters, 2004, 84, 2506-2508.	3.3	59
30	Room-temperature operation type-II GaSb/GaAs quantum-dot infrared light-emitting diode. Applied Physics Letters, 2010, 96, .	3.3	55
31	Band lineup inGaAs1â^'xSbx/GaAs strained-layer multiple quantum wells grown by molecular-beam epitaxy. Physical Review B, 1988, 38, 10571-10577.	3.2	54
32	Effects of thermal annealing on the luminescence and structural properties of high indium-content InGaN/GaN quantum wells. Applied Physics Letters, 2000, 76, 3902-3904.	3.3	54
33	High-Performance AlGaN/GaN Schottky Diodes With an AlGaN/AlN Buffer Layer. IEEE Electron Device Letters, 2011, 32, 1519-1521.	3.9	51
34	Improving the characteristics of intermediate-band solar cell devices using a vertically aligned InAs/GaAsSb quantum dot structure. Solar Energy Materials and Solar Cells, 2012, 105, 237-241.	6.2	51
35	Infrared photoluminescence of InAs epilayers grown on GaAs and Si substrates. Journal of Applied Physics, 1989, 65, 4079-4081.	2.5	49
36	Breakdown behavior of GaAs/AlGaAs HBTs. IEEE Transactions on Electron Devices, 1989, 36, 2165-2172.	3.0	47

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37	Theoretical study of the temperature dependence of 1.3-Î¼m AlGaInAs-InP multiple-quantum-well lasers. IEEE Journal of Quantum Electronics, 1996, 32, 2133-2138.	1.9	46
38	Terahertz Microchip for Illicit Drug Detection. IEEE Photonics Technology Letters, 2006, 18, 2254-2256.	2.5	44
39	Multiple-component photoluminescence decay caused by carrier transport in InGaN/GaN multiple quantum wells with indium aggregation structures. Applied Physics Letters, 2002, 80, 4375-4377.	3.3	43
40	Temperature dependence of the radiative recombination zone in InGaN/GaN multiple quantum well light-emitting diodes. Journal of Applied Physics, 2001, 89, 6554-6556.	2.5	42
41	Luminescence efficiency of InGaN multiple-quantum-well ultravioletlight-emitting diodes. Applied Physics Letters, 2004, 84, 5249-5251.	3.3	42
42	Carrier dynamics of type-II InAsâˆ•GaAs quantum dots covered by a thin GaAs1âˆ’xSbx layer. Applied Physics Letters, 2008, 93, .	3.3	41
43	Effects of thermal annealing on the emission properties of type-II InAs/GaAsSb quantum dots. Applied Physics Letters, 2009, 94, 053101.	3.3	40
44	Schottky rectifiers fabricated on free-standing GaN substrates. Solid-State Electronics, 2001, 45, 405-410.	1.4	36
45	On the origin of spin loss in GaMnN/InGaN light-emitting diodes. Applied Physics Letters, 2004, 84, 2599-2601.	3.3	36
46	SiO[sub 2]/Gd[sub 2]O[sub 3]/GaN Metal Oxide Semiconductor Field Effect Transistors. Journal of the Electrochemical Society, 2001, 148, G303.	2.9	35
47	Light output improvement of InGaN ultraviolet light-emitting diodes by using wet-etched stripe-patterned sapphire substrates. Journal of Applied Physics, 2007, 102, 084503.	2.5	35
48	Quantum-confined Stark shift in electroreflectance of InAs/InxGa1âˆ’xAs self-assembled quantum dots. Applied Physics Letters, 2001, 78, 1760-1762.	3.3	34
49	Two-dimensional nanoultrasonic imaging by using acoustic nanowaves. Applied Physics Letters, 2006, 89, 043106.	3.3	34
50	AlGaN/GaN high electron mobility transistors for proteinâ€“peptide binding affinity study. Biosensors and Bioelectronics, 2013, 41, 717-722.	10.1	34
51	Design and Demonstration of Tunable Amplified Sensitivity of AlGaN/GaN High Electron Mobility Transistor (HEMT)-Based Biosensors in Human Serum. Analytical Chemistry, 2019, 91, 5953-5960.	6.5	34
52	Temperature dependence of GaN high breakdown voltage diode rectifiers. Solid-State Electronics, 2000, 44, 613-617.	1.4	32
53	Transport in a gated Al0.18Ga0.82N/GaN electron system. Journal of Applied Physics, 2003, 94, 3181-3184.	2.5	32
54	Low Damage,>tex<$hbox Cl_2$>/tex<-Based Gate Recess Etching for 0.3->tex<$muhbox m$>/tex<Gate-Length AlGaN/GaN HEMT Fabrication. IEEE Electron Device Letters, 2004, 25, 52-54.	3.9	31

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55	Optical piezoelectric transducer for nano-ultrasonics. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2005, 52, 1404-1414.	3.0	31
56	Laser emission from GaN photonic crystals. Applied Physics Letters, 2006, 89, 071116.	3.3	31
57	Effects of GaAsSb capping layer thickness on the optical properties of InAs quantum dots. Applied Physics Letters, 2011, 99, 073108.	3.3	31
58	Passivation of GaSb using molecular beam epitaxy Y2O3 to achieve low interfacial trap density and high-performance self-aligned inversion-channel p-metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2014, 105, .	3.3	31
59	Growth and transport properties of InAs epilayers on GaAs. Applied Physics Letters, 1988, 53, 1647-1649.	3.3	30
60	Effects of Lens Shape on GaN Grown on Microlens Patterned Sapphire Substrates by Metallorganic Chemical Vapor Deposition. Journal of the Electrochemical Society, 2010, 157, H304.	2.9	30
61	Surface and bulk leakage currents in high breakdown GaN rectifiers. Solid-State Electronics, 2000, 44, 619-622.	1.4	29
62	Optical properties of indium nitride nanorods prepared by chemical-beam epitaxy. Nanotechnology, 2006, 17, 3930-3932.	2.6	29
63	Photogeneration of coherent shear phonons in orientated wurtzite semiconductors by piezoelectric coupling. Physical Review B, 2009, 80, .	3.2	29
64	Enumeration of circulating tumor cells and investigation of cellular responses using aptamer-immobilized AlGaN/GaN high electron mobility transistor sensor array. Sensors and Actuators B: Chemical, 2018, 257, 96-104.	7.8	29
65	Stimulated-emission spectra of high-indium-content InGaN/GaN multiple-quantum-well structures. Applied Physics Letters, 2000, 77, 3758-3760.	3.3	27
66	Catalyst-free growth of indium nitride nanorods by chemical-beam epitaxy. Applied Physics Letters, 2006, 88, 233111.	3.3	27
67	Single photon emission from an InGaAs quantum dot precisely positioned on a nanoplane. Applied Physics Letters, 2007, 90, 073105.	3.3	27
68	Light Output Enhancement of InGaN Light-Emitting Diodes Grown on Masklessly Etched Sapphire Substrates. IEEE Photonics Technology Letters, 2008, 20, 1621-1623.	2.5	27
69	Electrical properties of InAs epilayers grown by molecular beam epitaxy on Si substrates. Applied Physics Letters, 1988, 53, 562-564.	3.3	26
70	On the microstructure and interfacial structure of InSb layers grown on GaAs(100) by molecular beam epitaxy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1989, 60, 321-337.	0.6	26
71	Electroreflectance study on the polarization field in InGaN/AlInGaN multiple quantum wells. Applied Physics Letters, 2004, 84, 1114-1116.	3.3	26
72	Enhanced thermal stability and emission intensity of InAs quantum dots covered by an InGaAsSb strain-reducing layer. Applied Physics Letters, 2006, 89, 243103.	3.3	26

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73	Broadband terahertz ultrasonic transducer based on a laser-driven piezoelectric semiconductor superlattice. Ultrasonics, 2012, 52, 1-4.	3.9	26
74	High-field modulated ion-selective field-effect-transistor (FET) sensors with sensitivity higher than the ideal Nernst sensitivity. Scientific Reports, 2018, 8, 8300.	3.3	26
75	Process study of chemically vapour-deposited SnOx (xâ‰ˆ2) films. Thin Solid Films, 1983, 106, 163-173.	1.8	25
76	Enhancing the quantum efficiency of InGaN green light-emitting diodes by trimethylindium treatment. Applied Physics Letters, 2008, 92, 161113.	3.3	25
77	Formation of self-organized In0.5Ga0.5As quantum dots on GaAs by molecular beam epitaxy. Journal of Crystal Growth, 1997, 175-176, 777-781.	1.5	24
78	Device characteristics of the GaN/InGaN-doped channel HFETs. IEEE Electron Device Letters, 2001, 22, 501-503.	3.9	24
79	Effect of composition inhomogeneity on the photoluminescence of InGaN/GaN multiple quantum wells upon thermal annealing. Applied Physics Letters, 2002, 80, 1138-1140.	3.3	24
80	Effect of thermal annealing on high indium content InGaN/GaN single quantum well structures. Journal of Applied Physics, 2001, 89, 5465-5468.	2.5	23
81	Generation of frequency-tunable nanoacoustic waves by optical coherent control. Applied Physics Letters, 2005, 87, 093114.	3.3	23
82	Analysis of the Back-Gate Effect in Normally OFF p-GaN Gate High-Electron Mobility Transistor. IEEE Transactions on Electron Devices, 2015, 62, 507-511.	3.0	23
83	High-brightness inverted InGaN-GaN multiple-quantum-well light-emitting diodes without a transparent conductive layer. IEEE Electron Device Letters, 2003, 24, 156-158.	3.9	22
84	Currentâ€“voltage and reverse recovery characteristics of bulk GaN p-i-n rectifiers. Applied Physics Letters, 2003, 83, 2271-2273.	3.3	22
85	Anharmonic decay of subterahertz coherent acoustic phonons in GaN. Applied Physics Letters, 2007, 90, 041902.	3.3	22
86	Wavelength demultiplexing heterojunction phototransistor. Electronics Letters, 1990, 26, 1857.	1.0	21
87	Growth and Device Performance of GaN Schottky Rectifiers. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	21
88	Electron distribution and level occupation in an ensemble ofInxGa1â^’xAs/GaAsself-assembled quantum dots. Physical Review B, 2000, 62, 13040-13047.	3.2	21
89	Optical properties of InAs quantum dots with InAlAsâˆ•InGaAs composite matrix. Journal of Applied Physics, 2005, 97, 024312.	2.5	21
90	Sb-based semiconductors for low power electronics. Journal of Materials Chemistry C, 2013, 1, 4616.	5.5	21

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91	Extremely low nonalloyed and alloyed contact resistance using an InAs cap layer on InGaAs by molecularâ€beam epitaxy. Journal of Applied Physics, 1988, 64, 429-431.	2.5	20
92	High-responsivity InGaAs MSM photodetectors with semi-transparent Schottky contacts. IEEE Photonics Technology Letters, 1995, 7, 1333-1335.	2.5	20
93	1.55Î¼m emission from InAs quantum dots grown on GaAs. Applied Physics Letters, 2005, 87, 151903.	3.3	19
94	Low-resistance smooth-surface Ti/Al/Cr/Mo/Au n-type Ohmic contact to AlGaN/GaN heterostructures. Applied Physics Letters, 2009, 94, .	3.3	19
95	Direct detection of DNA using electrical double layer gated high electron mobility transistor in high ionic strength solution with high sensitivity and specificity. Sensors and Actuators B: Chemical, 2018, 271, 110-117.	7.8	19
96	High optical property vertically aligned InAs quantum dot structures with GaAsSb overgrown layers. Journal of Crystal Growth, 2011, 323, 164-166.	1.5	18
97	Suppression of emitter size effect on the currentâ€voltage characteristics of AlGaAs/GaAs heterojunction bipolar transistors. Applied Physics Letters, 1990, 56, 937-939.	3.3	17
98	Response to â€œComment on â€˜AlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxyâ€™â€‰â€•[Appl. Phys. Lett. 83, 3626 (2003)]. Applied Physics Letters, 2003, 83, 3628-3628.	3.3	17
99	InGaNâ€“GaN MQW LEDs With Current Blocking Layer Formed by Selective Activation. IEEE Electron Device Letters, 2004, 25, 384-386.	3.9	17
100	Characterizing the nanoacoustic superlattice in a phonon cavity using a piezoelectric single quantum well. Applied Physics Letters, 2006, 89, 143103.	3.3	17
101	Growth and characterization of crack-free semipolar {1-101}InGaNâˆ•GaN multiple-quantum well on V-grooved (001)Si substrates. Applied Physics Letters, 2008, 92, .	3.3	17
102	Low Turn-On Voltage and High-Current $hbox{InP}/ hbox{In}_{0.37}hbox{Ga}_{0.63}hbox{As}_{0.89}hbox{Sb}_{0.11}/hbox{In}_{0.53}hbox{Ga}_{0.47}hbox{As}$ Double Heterojunction Bipolar Transistors. IEEE Electron Device Letters, 2008, 29, 655-657.	3.9	17
103	Efficiency Enhancement of InGaN LEDs With an n-Type AlGaN/GaN/InGaN Current Spreading Layer. IEEE Electron Device Letters, 2011, 32, 1409-1411.	3.9	17
104	Low-<tex>$kappa$</tex>BCB Passivation on AlGaNâ€“GaN HEMT Fabrication. IEEE Electron Device Letters, 2004, 25, 763-765.	3.9	16
105	Pinholelike defects in multistack 1.3Î¼m InAs quantum dot laser. Journal of Applied Physics, 2006, 99, 114514.	2.5	16
106	A 600 V AlGaN/GaN Schottky barrier diode on silicon substrate with fast reverse recovery time. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 949-952.	0.8	16
107	Human immunodeficiency virus drug development assisted with AlGaN/GaN high electron mobility transistors and binding-site models. Applied Physics Letters, 2013, 102, 173704.	3.3	16
108	Dynamic monitoring of transmembrane potential changes: a study of ion channels using an electrical double layer-gated FET biosensor. Lab on A Chip, 2018, 18, 1047-1056.	6.0	16

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109	Suppression of electron and hole leakage in 1.3 Î¼m AlGaInAs/InP quantum well lasers using multiquantum barrier. Applied Physics Letters, 1998, 72, 2090-2092.	3.3	15
110	Excitation Density and Temperature Dependent Photoluminescence of InGaAs Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 1999, 38, 554-557.	1.5	15
111	InAs/GaAs quantum dot lasers with InGaP cladding layer grown by solid-source molecular-beam epitaxy. Applied Physics Letters, 2002, 80, 535-537.	3.3	15
112	InGaAsSb/InP Double Heterojunction Bipolar Transistors Grown by Solid-Source Molecular Beam Epitaxy. IEEE Electron Device Letters, 2007, 28, 679-681.	3.9	15
113	Simulation and fabrication of high voltage AlGaN/GaN based Schottky diodes with field plate edge termination. Microelectronic Engineering, 2007, 84, 2907-2915.	2.4	15
114	High-speed InGaAs metal-semiconductor-metal photodetectors with improved responsivity and process yield. Optical and Quantum Electronics, 1996, 28, 1327-1334.	3.3	14
115	High-reflectivity Pdâˆ•Niâˆ•Alâˆ•Tiâˆ•Au ohmic contacts to p-type GaN for ultraviolet light-emitting diodes. Applied Physics Letters, 2004, 85, 2797-2799.	3.3	14
116	Reflection property of nano-acoustic wave at the airâˆ•GaN interface. Applied Physics Letters, 2004, 85, 4735-4737.	3.3	14
117	Enhancing the optical properties of InAs quantum dots by an InAlAsSb overgrown layer. Applied Physics Letters, 2007, 91, 153106.	3.3	14
118	Nonresonant carrier transfer in single InGaAs/GaAs quantum dot molecules. Physical Review B, 2008, 77, .	3.2	14
119	Stimulated emission study of InGaN/GaN multiple quantum well structures. Applied Physics Letters, 2000, 76, 318-320.	3.3	13
120	Mechanisms for photon-emission enhancement with silicon doping in InGaN/GaN quantum-well structures. Journal of Electronic Materials, 2003, 32, 375-381.	2.2	13
121	Crack-free GaN grown on AlGaNâˆ•(111)Si micropillar array fabricated by polystyrene microsphere lithography. Applied Physics Letters, 2007, 91, 261910.	3.3	13
122	Surface Passivation of GaSb(100) Using Molecular Beam Epitaxy of Y₂O₃and Atomic Layer Deposition of Al₂O₃: A Comparative Study. Applied Physics Express, 2013, 6, 121201.	2.4	13
123	Matrix-dependent structural and photoluminescence properties of In0.5Ga0.5As quantum dots grown by molecular beam epitaxy. Solid-State Electronics, 1998, 42, 1331-1334.	1.4	12
124	Investigation of layered structure SAW devices fabricated using low temperature grown AlN thin film on GaN/sapphire. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2005, 52, 923-926.	3.0	12
125	Fabrication study of AlN solarâ€blind (<280â€‰nm) MSM photodetectors grown by lowâ€temperature deposition. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 224-228.	1.8	12
126	The impact of trimethylindium treatment time during growth interruption on the carrier dynamics of InGaN/GaN multiple quantum wells. Thin Solid Films, 2011, 519, 6092-6096.	1.8	12

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127	Trap-Profile Extraction Using High-Voltage Capacitanceâ€"Voltage Measurement in AlGaN/GaN Heterostructure Field-Effect Transistors With Field Plates. IEEE Transactions on Electron Devices, 2015, 62, 835-839.	3.0	12
128	Yellow-emitting Si-doped GaN: Favorable characteristics for intermediate band solar cells. Solar Energy Materials and Solar Cells, 2015, 132, 544-548.	6.2	12
129	A Comprehensive Model for Whole Cell Sensing and Transmembrane Potential Measurement Using FET Biosensors. ECS Journal of Solid State Science and Technology, 2018, 7, Q3001-Q3008.	1.8	12
130	High-performance large-area InGaAs MSM photodetectors with a pseudomorphic InGaP cap layer. IEEE Photonics Technology Letters, 1995, 7, 914-916.	2.5	11
131	Laser-Induced Activation of p-Type GaN with the Second Harmonics of a Nd:YAG Laser. Japanese Journal of Applied Physics, 2001, 40, 2143-2145.	1.5	11
132	Growth of low density InGaAs quantum dots for single photon sources by metalâ€"organic chemical vapour deposition. Nanotechnology, 2006, 17, 512-515.	2.6	11
133	The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1292-1297.	2.9	11
134	Device Characteristics of InGaSb/AlSb High-Hole-Mobility FETs. IEEE Electron Device Letters, 2012, 33, 964-966.	3.9	11
135	Optical and electrical properties of ZnSeO alloys grown by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 180-183.	1.5	11
136	Detection of Severe Acute Respiratory Syndrome (SARS) Coronavirus Nucleocapsid Protein Using AlGaN/GaN High Electron Mobility Transistors. ECS Transactions, 2013, 50, 239-243.	0.5	11
137	Gate leakage current induced trapping in AlGaN/GaN Schottky-gate HFETs and MISHFETs. Nanoscale Research Letters, 2014, 9, 474.	5.7	11
138	Direct detection of fibrinogen in human plasma using electric-double-layer gated AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2017, 111, .	3.3	11
139	Beyond the Limit of Ideal Nernst Sensitivity: Ultra-High Sensitivity of Heavy Metal Ion Detection with Ion-Selective High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2018, 7, Q176-Q183.	1.8	11
140	Temperature-dependent characteristics of 1.3-Î¼m AlGaInAs-InP lasers with multiquantum barriers at the guiding layers. IEEE Photonics Technology Letters, 1998, 10, 1700-1702.	2.5	10
141	Improving the off-state characteristics and dynamic on-resistance of AlInN/AlN/GaN HEMTs with a GaN cap layer. Applied Physics Express, 2015, 8, 064102.	2.4	10
142	Influence of Point Defects on the Properties of Undoped and Ga-Doped ZnO Films Grown by Plasma-Assisted Molecular Beam Epitaxy in an O-Rich Environment. ECS Journal of Solid State Science and Technology, 2016, 5, Q222-Q225.	1.8	10
143	Design and Simulation of High Performance Lattice Matched Double Barrier Normally Off AlInGaN/GaN HEMTs. IEEE Journal of the Electron Devices Society, 2020, 8, 873-878.	2.1	10
144	Two-Component Photoluminescence Decay in InGaN/GaN Multiple Quantum Well Structures. Physica Status Solidi (B): Basic Research, 2001, 228, 121-124.	1.5	9

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145	Ultrafast carrier dynamics in an InGaN thin film. Journal of Applied Physics, 2005, 97, 033704.	2.5	9
146	Narrow-band detection of propagating coherent acoustic phonons in piezoelectric InGaNâˆ•GaN multiple-quantum wells. Applied Physics Letters, 2007, 91, 133101.	3.3	9
147	Luminescence mechanism and carrier dynamic studies of InGaN-based dichromatic light emitting diodes with ultraviolet and blue emissions. Thin Solid Films, 2008, 517, 909-915.	1.8	9
148	Enhanced Normal-Incident Absorption of Quantum-Dot Infrared Photodetectors With Smaller Quantum Dots. IEEE Photonics Technology Letters, 2008, 20, 1240-1242.	2.5	9
149	Characterization and Comparison of GaAs/AlGaAs Uni-Traveling Carrier and Separated-Transport-Recombination Photodiode Based High-Power Sub-THz Photonic Transmitters. IEEE Journal of Quantum Electronics, 2010, 46, 19-27.	1.9	9
150	Memory device application of wide-channel in-plane gate transistors with type-II GaAsSb-capped InAs quantum dots. Applied Physics Letters, 2013, 103, 143502.	3.3	9
151	Bottomâ€Up Nanoâ€heteroepitaxy of Waferâ€Scale Semipolar GaN on (001) Si. Advanced Materials, 2015, 27, 4845-4850.	21.0	9
152	Reduction of hole transit time in GaAs MSM photodetectors by p-type /spl delta/-doping. IEEE Photonics Technology Letters, 1996, 8, 1525-1527.	2.5	8
153	Room-Temperature Operation of In0.5Ga0.5As Quantum Dot Lasers Grown on Misoriented GaAs Substrates by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, 605-607.	1.5	8
154	Electrical and optical characteristics of the GaN light-emitting diodes with multiple-pair buffer layer. Solid-State Electronics, 2000, 44, 1483-1486.	1.4	8
155	Improved electroluminescence of InAs quantum dots with strain reducing layer. Journal of Crystal Growth, 2001, 227-228, 1044-1048.	1.5	8
156	Localized and quantum-well state excitons in AlInGaN laser-diode structure. Physical Review B, 2002, 66, .	3.2	8
157	Frequency tunability of terahertz photonic transmitters. Applied Physics Letters, 2006, 88, 093501.	3.3	8
158	Challenges and Opportunities in GaN and ZnO Devices and Materials [Scanning the Issue]. Proceedings of the IEEE, 2010, 98, 1113-1117.	21.3	8
159	Temperature-Dependent Characteristics of a GaN/InGaN/ZnO Heterojunction Bipolar Transistor. Journal of the Electrochemical Society, 2010, 157, H381.	2.9	8
160	Optical properties of InGaN/GaN multiple quantum wells with trimethylindium treatment during growth interruption. Journal of Crystal Growth, 2011, 325, 41-45.	1.5	8
161	High Breakdown Voltage and Low Thermal Effect Micromachined AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2014, 14, 726-731.	2.0	8
162	Low resistivity and low compensation ratio Ga-doped ZnO films grown by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 216-220.	1.5	8

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163	Overall performance improvement in GaAs MSM photodetectors by using recessed-cathode structure. IEEE Photonics Technology Letters, 1997, 9, 226-228.	2.5	7
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